

Docket No.: D414

#11 Response
M. Baunson
PATENT 9/7/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Takeshi Nogami : Confirmation No.: 7243
Serial No.: 09/579,340 : Art Unit: 2814
Filed: 5/25/2000 : Examiner: Vikki H. Trinh
For: INTEGRATED CIRCUIT :
CHIP WITH HIGH-
ASPECT RATIO VIAS

Box Non-Fee Amendment
Commissioner for Patents
Washington, D. C. 20231

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RESPONSE

Sir:

The following Remarks are submitted in response to the Office Action dated 06/03/2002.

REMARKS*Claim Rejections - 35 USC §103*

The Examiner rejected claims 1-20 under 35 USC §103(a) as being unpatentable over admitted prior art (figures 1A-1C and Specification, prior art discussion, pages 1-7, hereinafter "APA") in view of Wang et al. (USPN 5,629,237, hereinafter "Wang").

Applicant respectfully traverses the rejections since the Applicant's claimed combination, as exemplified in claim 1, includes limitations not disclosed in APA and/or Wang of:

"a dielectric layer formed over said semiconductor substrate and said semiconductor device, said dielectric layer having a channel opening and a via provided therein; said via having a via entrant angle formed from a rim of said channel opening to a rim of the via and a horizontal bottom of the channel opening of greater than about 69 degrees whereby said channel opening forms a collimator for said via and a depth and a cross-sectional